



IRFBE30L Information



For Reference Only

Part Number IRFBE30L Manufacturer Vishay Siliconix

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 800V 4.1A TO-262

Package TO-262-3 Long Leads, I2Pak, TO-262AA

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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IRFBE30L Specifications

Manufacturer Part Number IRFBE30L Manufacturer Vishay Siliconix Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-262-3 Long Leads, 12Pak, TO-262AA Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 800V Current - Continuous Drain (Id) @ 25°C 4.1A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250μA Gate Charge (Qg) (Max) @ Vgs 78nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1300pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 125W (Tc) Rds On (Max) @ Id, Vgs 3 Ohm @ 2.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole		
CategoryDiscrete Semiconductor ProductsTransistors - FETs, MOSFETs - SinglePackageTO-262-3 Long Leads, 12Pak, TO-262AASeries-FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)800VCurrent - Continuous Drain (Id) @ 25°C4.1A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs78nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1300pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)125W (Tc)Rds On (Max) @ Id, Vgs3 Ohm @ 2.5A, 10VOperating Temperature-55°C ~ 150°C (TJ)	Manufacturer Part Number	IRFBE30L
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TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)800VCurrent - Continuous Drain (Id) @ 25°C4.1A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs78nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1300pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)125W (Tc)Rds On (Max) @ Id, Vgs3 Ohm @ 2.5A, 10VOperating Temperature-55°C ~ 150°C (TJ)	Series	-
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Current - Continuous Drain (Id) @ 25°C 4.1A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250μA Gate Charge (Qg) (Max) @ Vgs 78nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1300pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 125W (Tc) Rds On (Max) @ Id, Vgs 3 Ohm @ 2.5A, 10V Operating Temperature -55°C ~ 150°C (TJ)	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On) $10V$ Vgs(th) (Max) @ Id $4V$ @ 250μ AGate Charge (Qg) (Max) @ Vgs $78n$ C @ $10V$ Input Capacitance (Ciss) (Max) @ Vds $1300p$ F @ $25V$ Vgs (Max) $\pm 20V$ FET Feature-Power Dissipation (Max) $125W$ (Tc)Rds On (Max) @ Id, Vgs $3 \text{ Ohm } @ 2.5A, 10V$ Operating Temperature -55 °C ~ 150 °C (TJ)	Drain to Source Voltage (Vdss)	800V
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Gate Charge (Qg) (Max) @ Vgs 78nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1300pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 125W (Tc) Rds On (Max) @ Id, Vgs 3 Ohm @ 2.5A, 10V Operating Temperature -55°C ~ 150°C (TJ)	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds 1300pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 125W (Tc) Rds On (Max) @ Id, Vgs 3 Ohm @ 2.5A, 10V Operating Temperature -55°C ~ 150°C (TJ)	Vgs(th) (Max) @ Id	4V @ 250μA
Vgs (Max) ± 20 VFET Feature-Power Dissipation (Max) 125 W (Tc)Rds On (Max) @ Id, Vgs 3 Ohm @ 2.5 A, 10 VOperating Temperature -55 °C ~ 150 °C (TJ)	Gate Charge (Qg) (Max) @ Vgs	78nC @ 10V
FET Feature - Power Dissipation (Max) 125W (Tc) Rds On (Max) @ Id, Vgs 3 Ohm @ 2.5A, 10V Operating Temperature -55°C ~ 150°C (TJ)	Input Capacitance (Ciss) (Max) @ Vds	1300pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 3 Ohm @ 2.5A, 10V Operating Temperature -55°C ~ 150°C (TJ)	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs $3 \text{ Ohm } @ 2.5\text{A}, 10\text{V}$ Operating Temperature $-55^{\circ}\text{C} \sim 150^{\circ}\text{C} \text{ (TJ)}$	FET Feature	-
Operating Temperature $-55^{\circ}\text{C} \sim 150^{\circ}\text{C} \text{ (TJ)}$	Power Dissipation (Max)	125W (Tc)
	Rds On (Max) @ Id, Vgs	3 Ohm @ 2.5A, 10V
Mounting Type Through Hole	Operating Temperature	-55°C ~ 150°C (TJ)
Wiodining Type	Mounting Type	Through Hole
Supplier Device Package I2PAK	Supplier Device Package	I2PAK
Package / Case TO-262-3 Long Leads, I2Pak, TO-262AA	Package / Case	TO-262-3 Long Leads, I2Pak, TO-262AA
Report errors?		Report errors?

IRFBE30L Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

IRFBE30L Payment Methods



















IRFBE30L Shipping Methods













If you have any question about IRFBE30L, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com